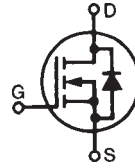


**Polar™ Power MOSFET**  
**HiPerFET™**
**IXFN52N90P**

 N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode


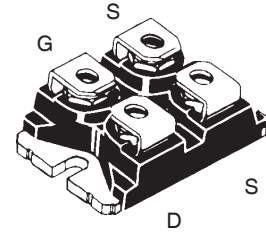
$$V_{DSS} = 900V$$

$$I_{D25} = 43A$$

$$R_{DS(on)} \leq 160m\Omega$$

$$t_{rr} \leq 300ns$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	900	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	900	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	43	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	104	A
$I_A$	$T_C = 25^\circ C$	26	A
$E_{AS}$	$T_C = 25^\circ C$	2	J
<b>dV/dt</b>	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	890	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS	$t = 1min$	2500 V~
	$I_{ISOL} \leq 1mA$	$t = 1s$	3000 V~
$M_d$	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

 miniBLOC, SOT-227  
 E153432

 G = Gate  
 S = Source  
 D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

**Features**

- International standard package
- miniBLOC, with Aluminium nitride isolation
- Avalanche Rated
- Low package inductance
- Fast intrinsic diode

**Advantages**

- Low gate drive requirement
- High power density

**Applications:**

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

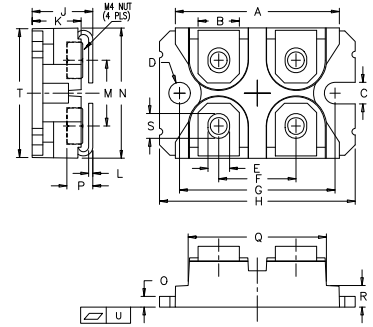
Symbol	Test Conditions ( $T_J = 25^\circ C$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	900		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	3.5		6.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$			50 $\mu A$
	$V_{GS} = 0V$			4 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 26A$ , Note 1			160 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 26\text{A}$ , Note 1	20	35	S
$R_{Gi}$	Gate input resistance		1.56	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		19	nF
$C_{oss}$			1180	pF
$C_{rss}$			24	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 26\text{A}$ $R_G = 1\Omega$ (External)		63	ns
$t_r$			80	ns
$t_{d(off)}$			95	ns
$t_f$			42	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 26\text{A}$		308	nC
$Q_{gs}$			117	nC
$Q_{gd}$			132	nC
$R_{thJC}$			0.14	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			56 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			208 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 26\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$			300 ns
$Q_{RM}$			1.8	$\mu\text{C}$
$I_{RM}$			26	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

### SOT-227B Outline



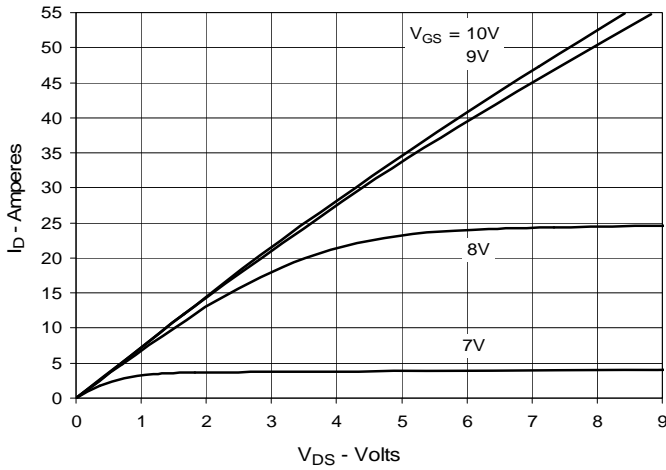
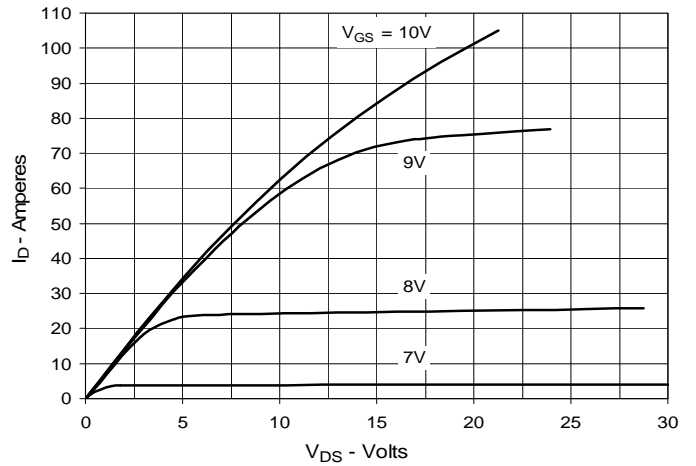
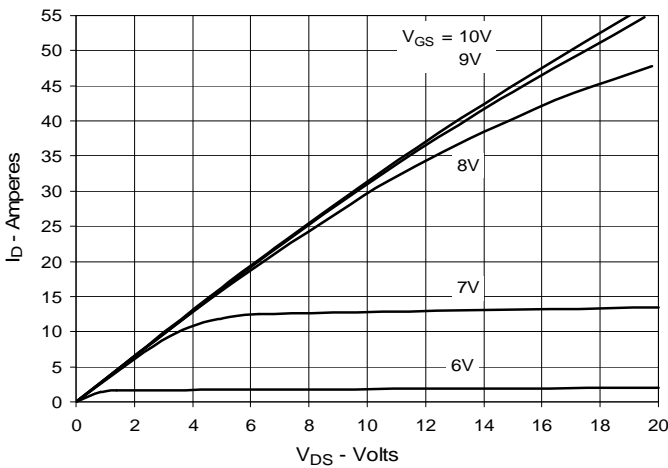
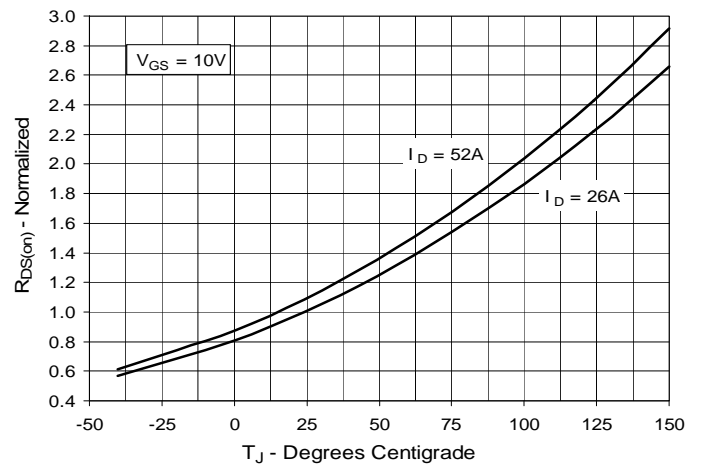
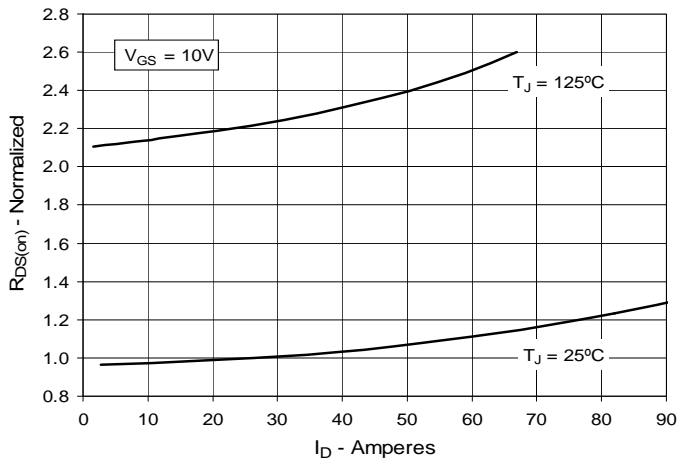
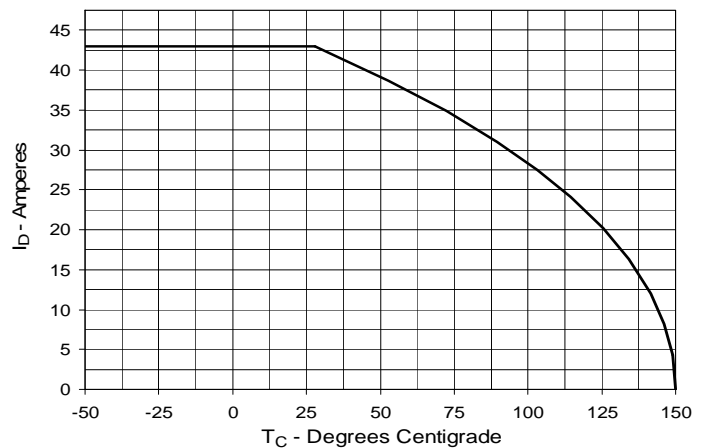
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

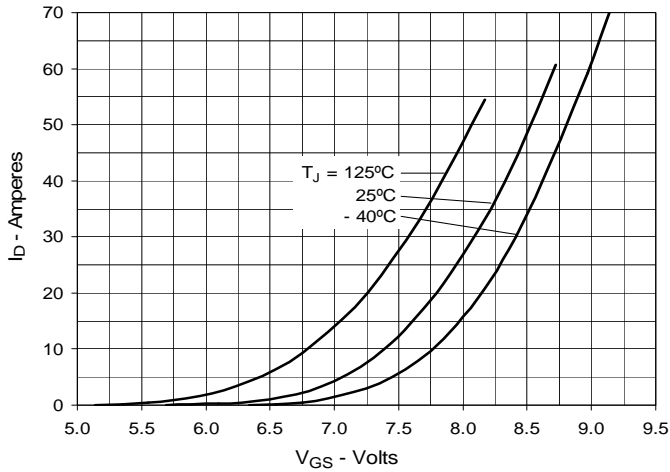
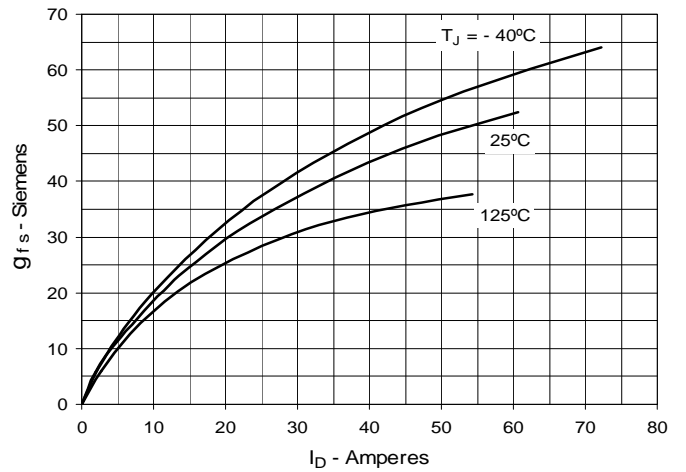
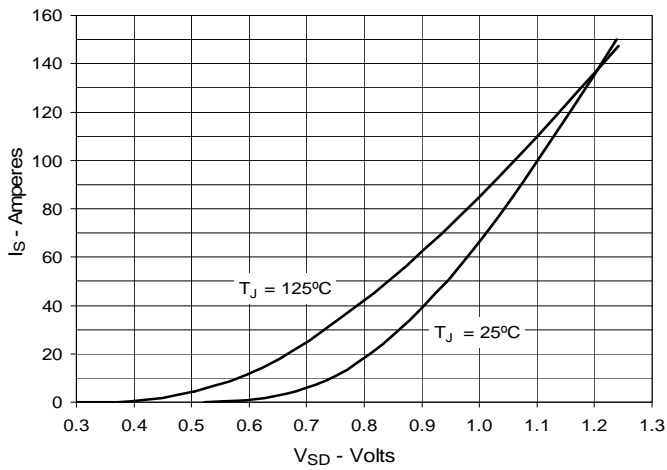
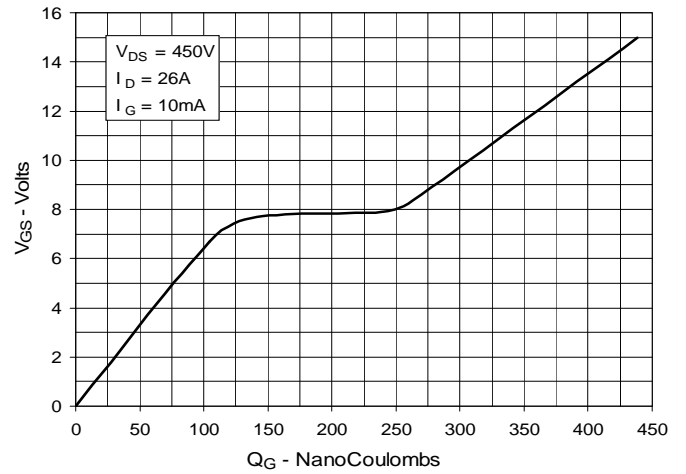
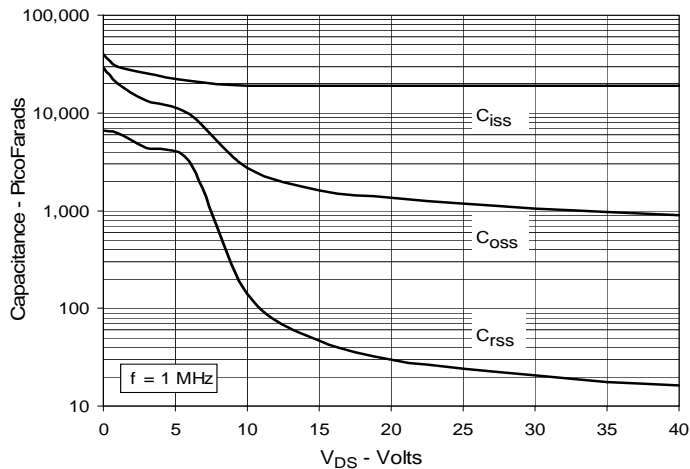
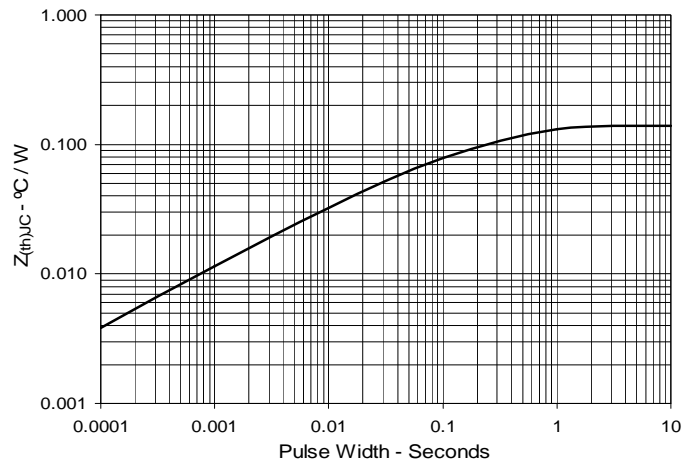
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @ 25°C**

**Fig. 2. Extended Output Characteristics @ 25°C**

**Fig. 3. Output Characteristics @ 125°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 26A$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 26A$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Maximum Transient Thermal Impedance**


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